

29 May 2003

09/809,295

L Number	Hits	Search Text	DB	Time stamp
-	1	809295.apn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 11:45
-	224	204/\$.ccls. and (deaerat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "de-aerated")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 14:31
-	99	(204/\$.ccls. and (deaerat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "de-aerated")) and membrane	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 11:47
-	25	(204/\$.ccls. and (deaerat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "de-aerated")) and diaphragm	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 11:52
-	132	(204/\$.ccls. and (deaerat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "de-aerated")) and (plating or plate or plated or electroplat\$3 or electrodeposit\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 11:53
-	18	((204/\$.ccls. and (deaerat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "de-aerated")) and diaphragm) and ((204/\$.ccls. and (deaerat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "de-aerated")) and (plating or plate or plated or electroplat\$3 or electrodeposit\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 11:53
-	63	(204/\$.ccls. and (deaerat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "de-aerated")) and (plating or plated or electroplat\$3 or electrodeposit\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:00
-	9	((204/\$.ccls. and (deaerat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "de-aerated")) and diaphragm) and ((204/\$.ccls. and (deaerat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "de-aerated")) and (plating or plated or electroplat\$3 or electrodeposit\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 11:59
-	33	((204/\$.ccls. and (deaerat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "de-aerated")) and membrane) and ((204/\$.ccls. and (deaerat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "de-aerated")) and (plating or plated or electroplat\$3 or electrodeposit\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 11:59
-	53	(204/\$.ccls. and (deaerat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "de-aerated")) and (plating or electroplat\$3 or electrodeposit\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 14:32
-	27	((204/\$.ccls. and (deaerat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "de-aerated")) and membran ) and ((204/\$.ccls. and (dea rat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "de-aerat d")) and (plating or electroplat\$3 or l ctrod posit\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 16:16

-	4896	204/228.1,228.6,232,237,238,242,252,263,264,266,275,277,278.ccls	US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:06
-	26	204/228.1,228.6,232,237,238,242,252,263,264,266,275,277,278.ccls and (deaerat\$3 or "de-aerat " or "d -aerating" or "de-aerator" or "de-aerated")	US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:26
-	1	US-20030057104-A1.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 13:51
-	2	JP-2001297744-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:29
-	1	2001JP-2001-297744	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:29
-	0	204/\$.ccls and (semiconductor or wafer) and diaphragm	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 14:24
-	274	204/\$.ccls. and (semiconductor or wafer) and diaphragm	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 14:25
-	1	(204/\$.ccls. and (deaerat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "de-aerated")) and (204/\$.ccls. and (semiconductor or wafer) and diaphragm)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 14:26
-	24	(204/\$.ccls. and (semiconductor or wafer) and diaphragm) and (remov\$3 near (gas or oxygen or "o.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 14:35
-	8	(204/\$.ccls. and (semiconductor or wafer) and diaphragm) and degas\$4 .	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 14:30
-	28	((204/\$.ccls. and (semiconductor or wafer) and diaphragm) and (remov\$3 near (gas or oxygen or "o.sub.2")))) ((204/\$.ccls. and (semiconductor or wafer) and diaphragm) and degas\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 14:31
-	1016	204/\$.ccls. and (deaerat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "de-aerated" or degas\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 14:31
-	166	(204/\$.ccls. and (deaerat\$3 or "de-aerate" or "de-aerating" or "de-aerator" or "d -aerated" or d gas\$4)) and (plating or electroplat\$3 or el ctrodeposit\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 14:32

-	22	((204/\$.ccls. and (deaerat\$3 or "de-a rate" or "de-aerating" or "d -aerator" or "de-aerated" or degas\$4)) and (plating or electroplat\$3 or electrodeposit\$3)) and diaphragm	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 14:32
-	37	(204/\$.ccls. and (semiconductor or wafer) and diaphragm) and ((remov\$3 or purg\$3) near (gas or oxygen or "o.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 14:38
-	13	((204/\$.ccls. and (semiconductor or wafer) and diaphragm) and ((remov\$3 or purg\$3) near (gas or oxygen or "o.sub.2"))) not (((204/\$.ccls. and (semiconductor or wafer) and diaphragm) and (remov\$3 near (gas or oxygen or "o.sub.2")))) ((204/\$.ccls. and (semiconductor or wafer) and diaphragm) and degas\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 14:38
-	97	204/\$.ccls. and (semiconductor or wafer) and seal and diaphragm	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 16:15
-	39	(204/\$.ccls. and (semiconductor or wafer) and seal and diaphragm) and (plating or electroplat\$3 or electrodeposit\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/29 09:44
-	36	((204/\$.ccls. and (semiconductor or wafer) and seal and diaphragm) and (plating or electroplat\$3 or electrodeposit\$3)) not (diaphragm adj pump)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 16:24
-	24	((204/\$.ccls. and (semiconductor or wafer) and seal and diaphragm) and (plating or electroplat\$3 or electrodeposit\$3)) not (diaphragm adj pump)) not (finger adj diaphragm)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 16:28
-	34	(204/\$.ccls. and (semiconductor or wafer) and seal and diaphragm) and (bubble or deaerat\$3 or degas\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 16:29
-	125	204/\$.ccls. and (((wafer or substrate) near holder) same seal)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/29 09:35
-	4	204/\$.ccls. and YOSHIOKA.in. and JUNICHIRO.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/29 09:43
-	235	204/\$.ccls. and (wafer or semiconductor) and ((oxygen or "o.sub.2") near (sensor or detector))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/29 09:44
-	49	(204/\$.ccls. and (wafer or semiconductor) and ((oxygen or "o.sub.2") n ar (sensor or detector))) and (plating or lectroplat\$3 or electrod posit\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/29 09:45